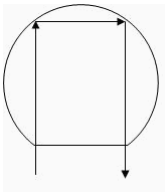
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.30 mm	
	2.0	Primary Flat Orientation	{110} +/- 1	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Length	18.00 +- 2.00 mm @ 90+- 5 deg	
	5.0	Overall Thickness	500.00 +/- 15.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process
	7.0	Bow	<40.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<40.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	None	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
	11.0	Frontsurface condition	Polished	Bright Light, 100% (note2)
	12.0	Backsurface condition	Polished	Bright Light, 100% (note2)
HandleSilicon	13.0	Handle Silicon Raw Material	Prime Silicon	
	14.0	Handle Growth Method	CZ	Wafer Vendor
	15.0	Handle Orientation	{100} +/- 0.5	Wafer Vendor
	16.0	Handle Thickness	500.00 +/- 15.00 µm	ADE, 100%
	17.0	Handle Doping Type	P	Wafer Vendor
	18.0	Handle Dopant	Boron	Wafer Vendor
	19.0	Handle Resistivity	0.01 ~ 0.02	Wafer Vendor
	19.1	Handle Silicon Dislocation Etch Pit Density	<100/cm2	Wafer Vendor
	20.0	Surface Haze	None	Bright Light, 100% (note 2)

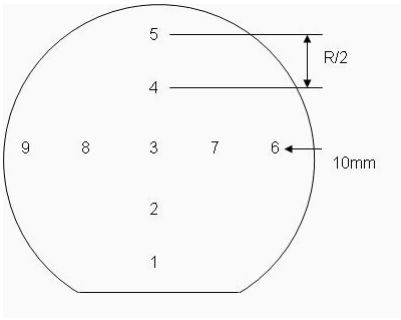
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information